

ABSTRACT

An inventive semiconductor integrated circuit device includes: an external connection terminal 1; an electrostatic discharge protection circuit 2; an output circuit 3; an output prebuffer circuit 4; an input prebuffer circuit 5; an internal circuit 41; an inter-power supply electrostatic discharge protection circuit 6; and a gate voltage control circuit 7. The gate voltage control circuit 7 has a capacitor 25 and a resistor 26, and the inter-power supply electrostatic discharge protection circuit 6 has an NMIS transistor 24. When a positive surge is applied to the external connection terminal 1, the gate potential of the NMIS transistor 24 is also increased. Thus, the NMIS transistor 24 is turned on, and the positive electrical charge supplied to the external connection terminal 1 is discharged toward a ground line 23.